Control of polarization and dipole moment in low-dimensional semiconductor nanostructures

Li, L.; Mexis, M.; Ridha, P.; Bozkurt, M.; Patriarche, G.; Smowton, P.M.; Blood, P.; Koenraad, P.M.; Fiore, A.

Published in:
Applied Physics Letters

DOI:
10.1063/1.3269592

Published: 01/01/2009

Document Version
Publisher’s PDF, also known as Version of Record (includes final page, issue and volume numbers)

Please check the document version of this publication:
• A submitted manuscript is the author’s version of the article upon submission and before peer-review. There can be important differences between the submitted version and the official published version of record. People interested in the research are advised to contact the author for the final version of the publication, or visit the DOI to the publisher's website.
• The final published version features the final layout of the paper including the volume, issue and page numbers.

Link to publication

Citation for published version (APA):
Control of polarization and dipole moment in low-dimensional semiconductor nanostructures

L. H. Li, M. Mexis, P. Ridha, M. Bozkurt, G. Patriarche, P. M. Smowton, P. Blood, P. M. Koenraad, and A. Fiore

1Ecole Polytechnique Federale de Lausanne, Institute of Photonics and Quantum Electronics, Station 3, CH-1015 Lausanne, Switzerland
2Cardiff University, The Parade, Cardiff CF24 3AA, United Kingdom
3COBRA Research Institute, Eindhoven University of Technology, P.O. Box 513, 5600 MB Eindhoven, The Netherlands
4LPN/CNRS, Route de Nozay, 91460 Marcoussis, France

(Received 15 September 2009; accepted 9 November 2009; published online 4 December 2009)

We demonstrate the control of polarization and dipole moment in semiconductor nanostructures, through nanoscale engineering of shape and composition. Rodlike nanostructures, elongated along the growth direction, are obtained by molecular beam epitaxial growth. By varying the aspect ratio and compositional contrast between the rod and the surrounding matrix, we rotate the polarization of the dominant interband transition from transverse-electric to transverse-magnetic, and modify the dipole moment producing a radical change in the voltage dependence of absorption spectra. This opens the way to the optimization of quantum dot amplifiers and electro-optical modulators. © 2009 American Institute of Physics. [doi:10.1063/1.3269592]

The control of the electronic and optical properties of semiconductor nanostructures is a formidable challenge, with major impact on practical applications of nanophotonics. While high-performance lasers, amplifiers, modulators, and detectors, as well as single-photon sources, have been obtained using epitaxial quantum dots (QDs), the Stranski–Krastanow (SK) growth method typically used offers little control over the QD shape and composition profile. This lack of control has a direct influence on two key macroscopic parameters: polarization and dipole moment. Indeed, SK QDs typically have a flat shape. This results in an asymmetric potential profile and in compressive strain, which both push states with large light-hole component away from the band-edge, producing a strongly in-plane polarized ground-state transition. This prevents the application of QDs in in-line semiconductor optical amplifiers (SOAs), where polarization insensitivity is needed. Moreover, the In composition profile along the growth direction, resulting from the complex interplay of nucleation and In segregation, determines the spatial localization of electrons and holes, and thus the dipole moment, which is a key parameter for application in electro-optical modulators. Dipole moments oriented both parallel and antiparallel to the growth direction have been observed in different types of QDs, but without a clear correlation to the structural properties and thus with no possibility of control.

A better possibility of control of the vertical composition profile exists in columnar quantum dots (CQDs), obtained by depositing a short-period GaAs/InAs superlattice (SL) on top of a seed QD layer. Selective adatom incorporation in the strained areas on top of seed QDs results in a tall, In-rich column within an InGaAs matrix. The CQD height, and the In profile along the growth direction can then be controlled by the GaAs and InAs layer thickness of the SL. While earlier generations of CQDs presented an approximately cubic shape, recent growth optimization has allowed the increase of the QD aspect ratio (height/diameter) > 1.6–9. The obtained nanostructures are more similar to quantum rods than to conventional QDs. The polarization of emission and gain from CQDs has been shown to gradually evolve from transverse-electric (TE) to transverse-magnetic (TM) as the height is increased but so far TM gain in SOAs has been obtained only in the InAs/InP system, where strain compensation in the barriers can be used to control the strain in the QDs. Evidence of modified dipole moment in compressive strain CQDs was also reported. In this letter, we report the electro-optical properties of a recent generation of InAs/GaAs CQDs with much increased aspect ratio and compositional contrast, leading to TM-dominant gain and lasing, and a radical change in the dipole moment and electroabsorption characteristics.

The CQDs were grown by molecular-beam epitaxy on GaAs (001) substrates, with the following growth sequence. A 1.8 monolayer (ML) InAs QD seed layer is first deposited, followed by a N-periods GaAs/InAs SL (thicknesses d_{GaAs} and d_{InAs}, respectively). The growth rates of GaAs and InAs were 0.7 and 0.1 ML/s, and the growth temperature was 500 °C. After growth of each InAs layer, a growth interruption of 5 s was applied in order to make the CQD size distribution more uniform. The In contents x_{CQD} and x_{2D} in the CQD and two-dimensional (2D) layer are determined by the InAs and GaAs thicknesses (d_{InAs} and d_{GaAs}) in the SL, and by the CQD formation process. We recently reported that d_{InAs} and d_{GaAs} can be varied in a narrow parameter space to control the compositions, while keeping a uniform CQD with high radiative quality. In particular, we are able to controllably tune x_{2D} in the 12%–16% range by varying d_{InAs} (d_{GaAs}) in the 0.62–0.95 (3–6) MLs range, while keeping x_{CQD} nearly constant. This control of x_{2D} in turn allows us to extend the rod height up to at least 70 nm, as compared to previously reported values around 40 nm.
Cross sectional scanning tunneling microscopy (X-STM) has been performed at room temperature on the CQDs with $N=30$ periods ($0.95\, \text{ML InAs}/6\, \text{ML GaAs}$) SL. The STM is performed in the constant current mode with $V=-3.3\, \text{V}$ applied to the sample and current set at $I=32\, \text{pA}$. The bright areas correspond to In-rich areas which have an outward relaxation proportional to the amount of In.

To further demonstrate TM-polarized optical gain, we tested ridge-waveguide laser structures ($3\, \text{mm}\times11\, \mu\text{m}$) under high injection. The active region is formed by three stacks of CQDs with $N=35$ periods ($0.95\, \text{ML InAs}/6\, \text{ML GaAs}$), separated by $100\, \text{nm}$ thick GaAs spacer layers. The emission spectra measured just above threshold (at $1.1\, \text{kA/cm}^2$) for the two polarizations are shown in Fig. 3, while the TM-polarized light-current curve is reported in the inset. The EL spectra are well distinct for TE and TM polarizations, with TM (TE) emission centered around 1190 (1140) nm. This confirms that the ground state transition involves valence band states with large light-hole component, while the states with large heavy-hole components are blue-shifted by $\approx 40\, \text{meV}$. A clear lasing peak is observed in TM polarization, at the peak of the TM amplified spontaneous emission spectra, while the much lower TE peak is due to the finite extinction ratio of the polarizer. The demonstration of TM lasing is a clear evidence of TM-dominant gain in these InAs/GaAs CQDs, which has never been reported before in compressive strain material systems.
We further investigated the dipole moment in different CQD structures by studying the quantum-confined Stark effect (CQSE) by waveguide photocurrent spectroscopy under electric field. All measurements were taken at room temperature. For the lower aspect ratio CQD sample (N=18 periods) in Fig. 4(a), the photoabsorption edge is redshifted with increasing bias, the amplitude of the shift being enhanced as compared to that of a conventional QD. The number of states in a larger dot is greater while the spatial separation of electron and hole wave functions, determining their transition oscillator strength, change very rapidly with applied electric field. All measurements were taken at room temperature. The energy shift of reverse bias for CQDs with N=30 periods SL. The observed features clearly indicate that the sign and amplitude of the dipole moment can be controlled by the CQD aspect ratio, opening the way to its nanoscale engineering, with possible application to electro-optic modulators.

In conclusion, we have demonstrated how the combined control of shape and composition of semiconductor nanostructures can be used to manipulate their polarization and electro-optical properties. By varying the aspect ratio and compositional contrast between the CQD and its surrounding matrix, we have obtained TM-polarized lasing and changing the dipole moment in compressive strain material systems. This type of nanoscale engineering will be a key tool for practical applications of QDs.

We acknowledge financial support from the EU-FP6 Project ZODIAC (Contract No. FP6/017140) and the Swiss National Science Foundation.

17E. P. O’Reilly (private communication).

FIG. 4. (Color online) Room temperature photocurrent spectra at various reverse bias for CQDs with (a) N=18 and (b) N=30 periods SL.

The observed features clearly indicate that the sign and amplitude of the dipole moment can be controlled by the CQD aspect ratio, opening the way to its nanoscale engineering, with possible application to electro-optic modulators.